

ABSTRACT

A method for forming an integrated circuit is provided. A semiconductor film is formed onto a first substrate. A metal film
5 is formed onto a second substrate. The second substrate is bonded with the metal film onto the thin film of the first substrate. A first layer of transistors is formed onto the film. The second substrate is removed at a temperature within a low temperature range. The semiconductor film is bonded with the first layer of
10 transistors onto a second layer of transistors of a third substrate.

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